

16. (New) The method of claim 5, wherein the semiconductor layer is formed by supplying a material gas heated to a temperature of 1020°C.

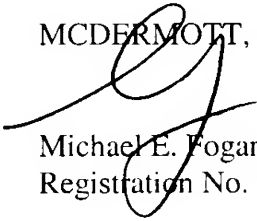
17. (New) The method of claim 7, wherein the semiconductor layer is formed by supplying a material gas heated to a temperature of 1020°C.

REMARKS

In the preliminary amendment, Applicants have submitted new claims 14-17 for consideration. Applicants submit that new claims 14-17 are in condition for allowance, an indication for which is respectfully solicited. No new matter has been added.

Respectfully submitted,

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